

Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	416207	eeeprom or flash or nonvolatile	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 15:15
L2	227024	source and drain and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 15:16
L3	104505	source near2 region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 15:16
L4	92341	drain near2 region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 15:16
L5	2005175	substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 15:16
L6	531772	insulat\$3 near2 (film or layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 15:17
L7	3269866	electron or hole	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 15:17
L8	10153	erase near2 operation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 15:18

L9	12572	charge near2 accumulation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 15:18
L10	29580	1 and 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 15:18
L11	13848	10 and 3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 15:19
L12	13040	11 and 4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 15:19
L13	12120	12 and 5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 15:19
L14	8011	13 and 6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 15:19
L15	6325	14 and 7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 15:20
L16	1589	15 and 8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 15:20

L17	87	16 and 9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 15:20
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